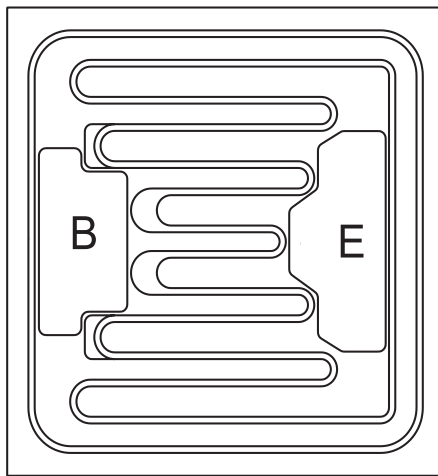


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	31 x 31 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	5.9 x 11.8 MILS
Emitter Bonding Pad Area	6.5 x 13.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR R1

GROSS DIE PER 4 INCH WAFER

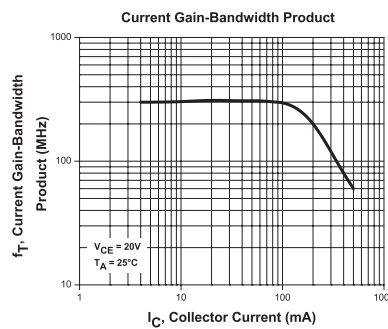
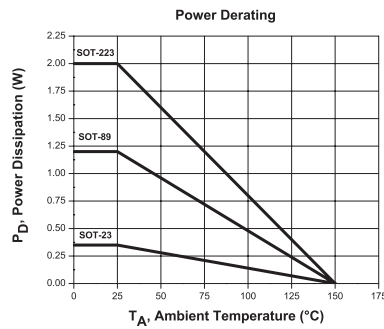
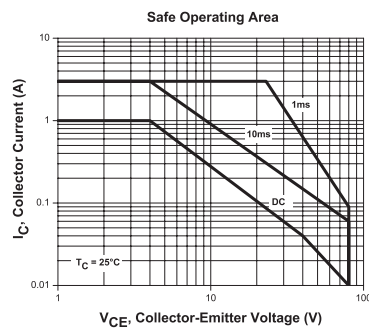
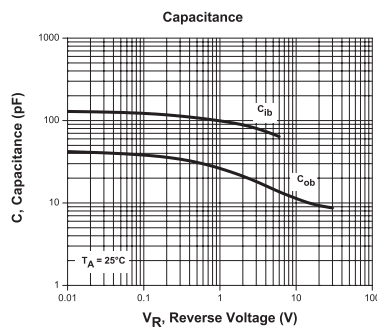
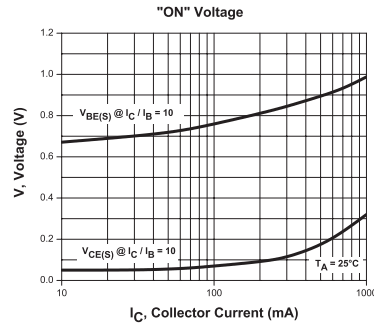
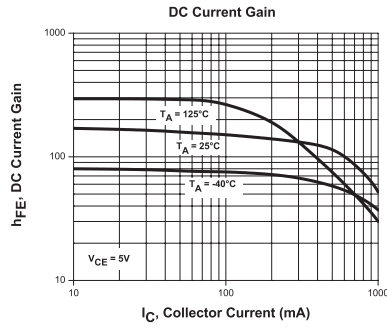
11,300

PRINCIPAL DEVICE TYPES

2N4033
CMPT4033
CXT4033
CZT4033

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R3 (23-August 2006)



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